



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

RS2AA-AAF~RS2MA-AAF

SMA Fast Recovery Diode 快恢复二极管



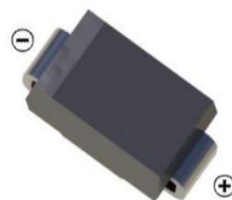
■Features 特点

Glass Passivated Chip Junction 玻璃钝化芯片结

Fast Recovery time 快恢复时间

Surface mount device 表面贴装器件

Case 封装:SMA



■Maximum Rating 最大额定值

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	RS2AA-AAF	RS2BA-AAF	RS2DA-AAF	RS2GA-AAF	RS2JA-AAF	RS2KA-AAF	RS2M-AAFA	Unit 单位
Marking 印字		RS2A	RS2B	RS2D	RS2G	RS2J	RS2K	RS2M	
Repetitive Peak Reverse Voltage 重复峰值反向电压	V _{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I _F	2							A
Peak Surge Current 峰值浪涌电流	I _{FSM}	50							A
Thermal Resistance J-A 结到环境热阻	R _{θJA}	65							°C/W
Operating/Storage Temperature 工作温度和储藏温度范围	T _J , T _{stg}	-65to+150°C							°C

■Electrical Characteristics 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	RS2AA-RS2GA-AAF	RS2JA-AAF	RS2KA-RS2MA-AAF	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	1.3			V	I _F =2A
Reverse Current 反向电流	I _R	5(T _A =25°C) 300(T _A =125°C)			μA	V _R =V _{RRM}
Reverse Recovery Time 反向恢复时间	T _{rr}	150	250	500	nS	I _F =0.5A, I _R =1A I _{rr} =0.25A
Junction Capacitance 结电容	C _J	50			pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

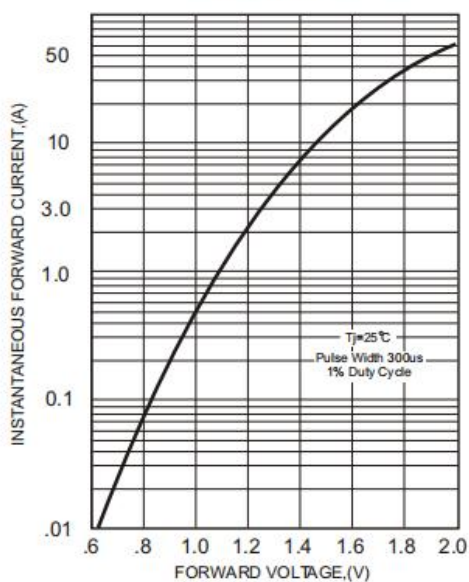


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

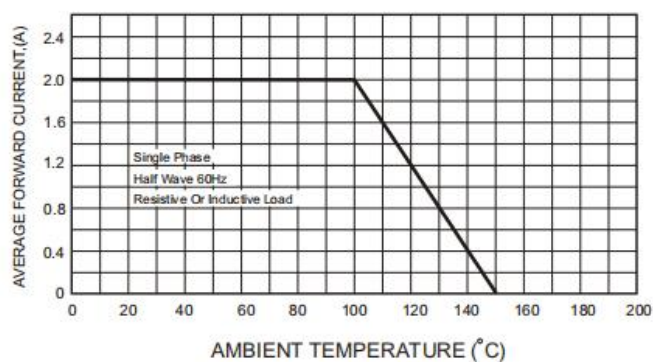
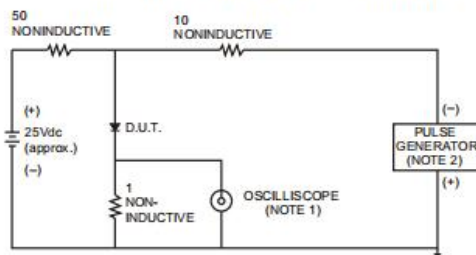


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm, 22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

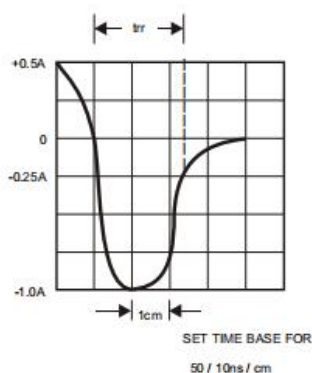


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

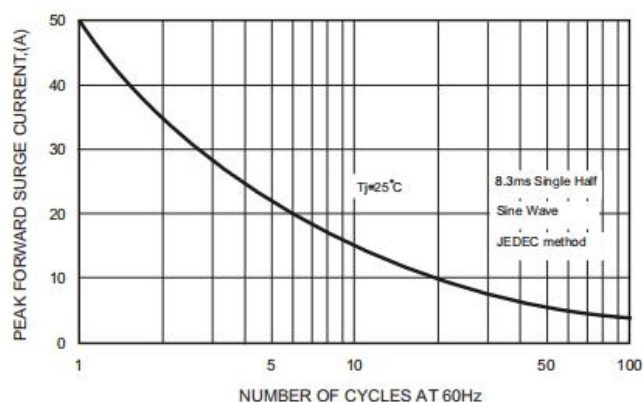
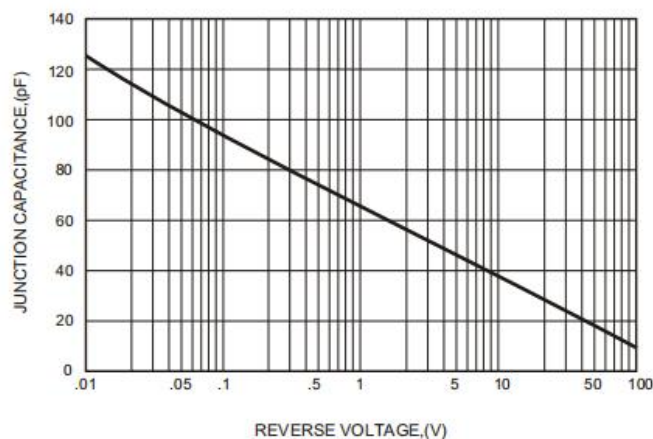
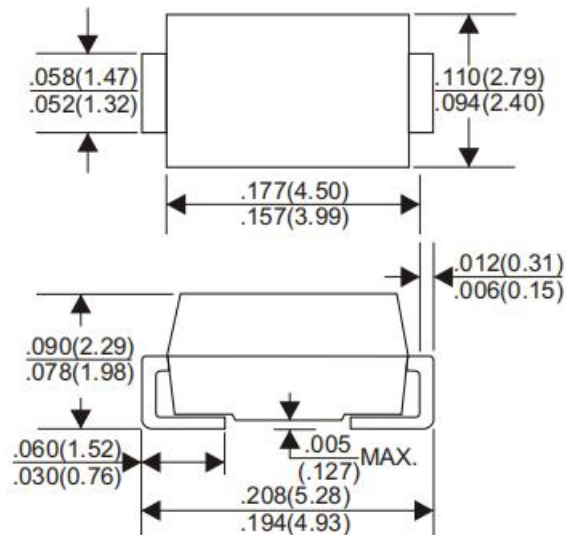


FIG.5-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸

DO-214AC(SMA)



Dimensions in inches and (millimeters)